

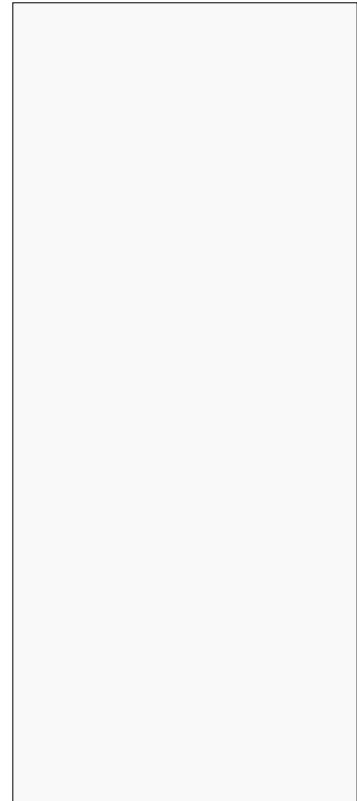


**JCT612TF 12A SCR**

Rev.A.1.1

**DESCRIPTION:**

JCT612TF silicon controlled rectifier is specifically designed for medium power switching and phase control applications. High current density due to mesa technology; SIPOS and Glass Passivation technology used has reliable operation up to 125 °C junction temperature. Low  $I_{GT}$  parts available. From all three terminals to external heatsink, JCT612TF provides a rated insulation voltage of 2000  $V_{RMS}$ , complying with UL standards (File ref: E252906).  
Package T

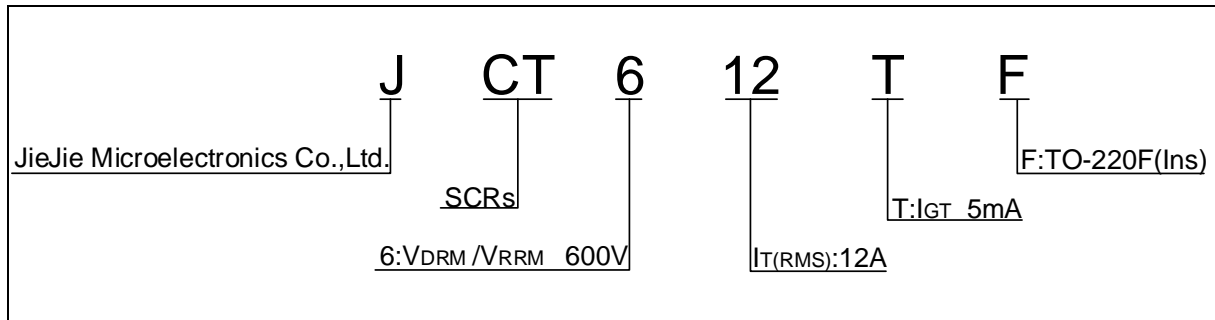


Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	0.5	kV

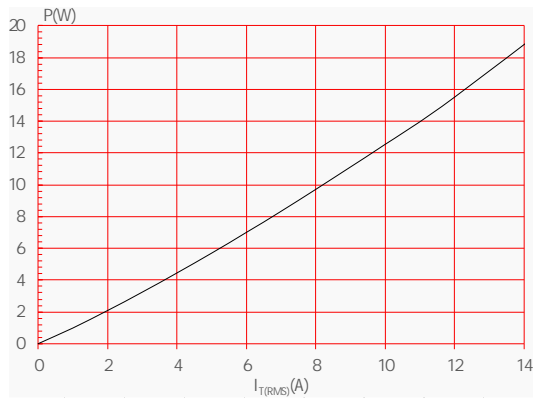
**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12V$ $R_{jlppM}$				A

ORDERING INFORMATION



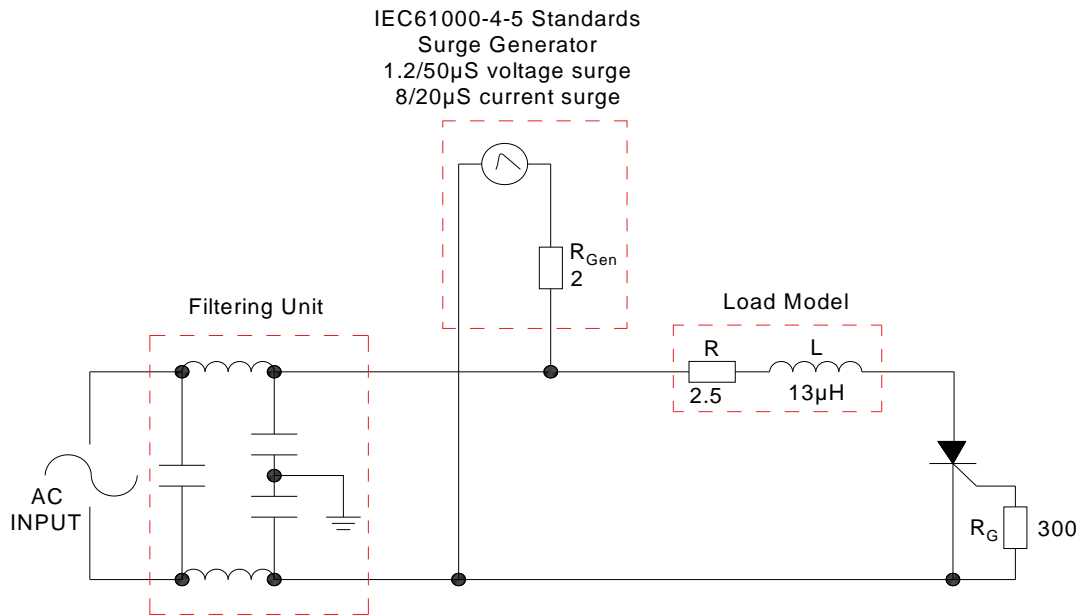
**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature



FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



## LEAD FORMING AND SOLDERING


Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.



**PACKAGE MECHANICAL DATA**



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